

isc N-Channel Mosfet Transistor

20N50

• FEATURES

- Drain Current $I_D = 20A @ T_C = 25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS} = 500V (Min)$
- Low ON Resistance $R_{DS(on)} = 0.27 \Omega (Max)$
- Low leakage current
- Fast Switching

• DESCRIPTION

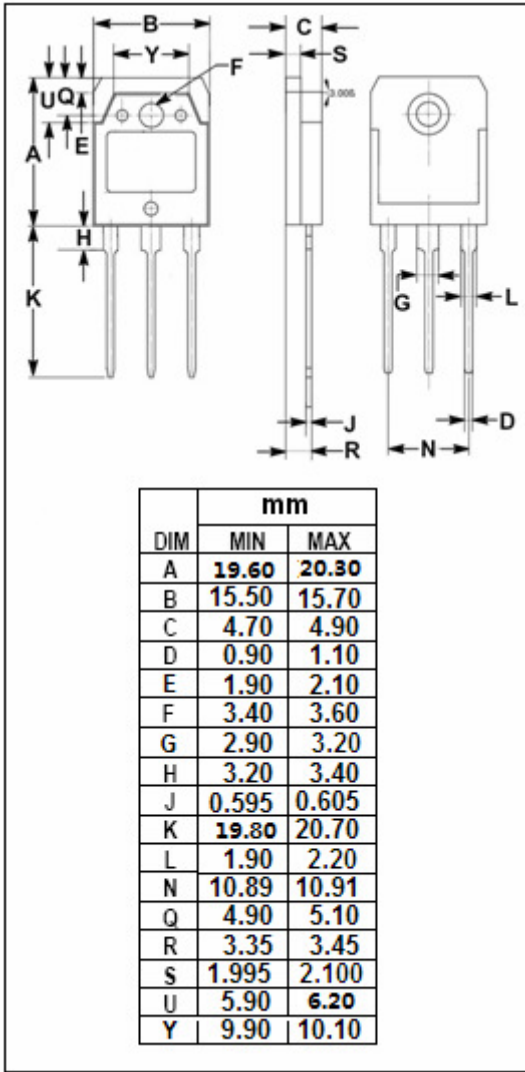
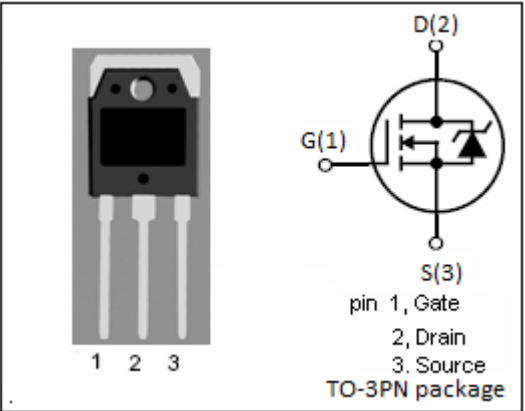
- Designed for high efficiency switch mode power supply.

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	20	A
I_{DM}	Drain Current-Single Plused	80	A
P_D	Power Dissipation	150	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature range	-55~150	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	0.833	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	50	$^{\circ}C/W$



isc N-Channel Mosfet Transistor**20N50****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	500		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 10A		0.27	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V; V _{GS} = 0		10	μA
V _{SD}	Forward On-Voltage	I _S = 20A; V _{GS} = 0		1.7	V